Voltage Regulator - Dual, Low I_Q, Low Dropout 150 mA

The NCV8152 is 150 mA, Dual Output Linear Voltage Regulator. Device provides a very stable and accurate voltage with ultra low noise and very high Power Supply Rejection Ratio (PSRR) suitable for RF applications. The NCV8152 is suitable for powering RF blocks of automotive infotainment systems and other power sensitive device. Due to low power consumption the NCV8152 offers high efficiency and low thermal dissipation.

Features

- Operating Input Voltage Range: 1.9 V to 5.25 V
- Two Independent Output Voltages: (for details please refer to the Ordering Information section)
- Very Low Dropout: 150 mV Typical at 150 mA
- Low IQ of typ. 50 µA per Channel
- High PSRR: 75 dB at 1 kHz
- Two Independent Enable Pins
- Thermal Shutdown and Current Limit Protections
- Stable with a 0.22 µF Ceramic Output Capacitor
- Available in XDFN6 1.2 x 1.2 mm Package
- Active Output Discharge for Fast Output Turn-Off
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable; Device Temperature Grade 1: -40°C to +125°C Ambient Operating Temperature Range
- These are Pb–Free Devices

Typical Applications

- Wireless LAN, Bluetooth®, ZigBee® Interfaces
- Parking Camera Modules
- Automotive Infotainment Systems

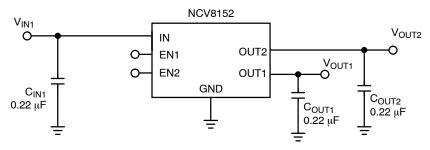


Figure 1. Typical Application Schematic



ON Semiconductor®

www.onsemi.com



XDFN6, 1.2x1.2 CASE 711AT

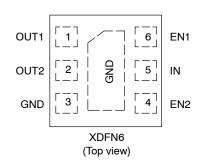


MARKING

SE 711AT

XX = Specific Device Code M = Date Code





ORDERING INFORMATION

See detailed ordering and shipping information on page 16 of this data sheet.

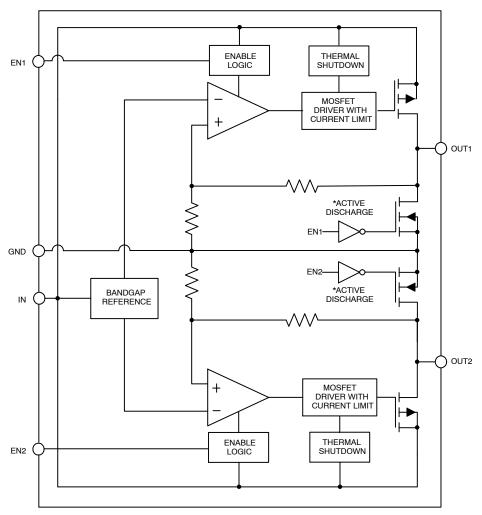


Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No. XDFN6	Pin Name	Description
1	OUT1	Regulated output voltage of the first channel. A small 0.22 μF ceramic capacitor is needed from this pin to ground to assure stability.
2	OUT2	Regulated output voltage of the second channel. A small 0.22 μF ceramic capacitor is needed from this pin to ground to assure stability.
3	GND	Power supply ground. Soldered to the copper plane allows for effective heat dissipation.
4	EN2	Driving EN2 over 0.9 V turns-on OUT2. Driving EN below 0.4 V turns-off the OUT2 and activates the active discharge.
5	IN	Input pin common for both channels. It is recommended to connect 0.22 μF ceramic capacitor close to the device pin.
6	EN1	Driving EN1 over 0.9 V turns-on OUT1. Driving EN below 0.4 V turns-off the OUT1 and activates the active discharge.
-	EP	Exposed pad must be tied to ground. Soldered to the copper plane allows for effective thermal dissipation.

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	–0.3 V to 6 V	V
Output Voltage	V _{OUT1} , V _{OUT2}	–0.3 V to VIN + 0.3 V or 6 V	V
Enable Inputs	V _{EN1} , V _{EN2}	–0.3 V to VIN + 0.3 V or 6 V	V
Output Short Circuit Duration	t _{SC}	Indefinite	S
Operating Ambient Temperature Range	T _A	-40 to +125	°C
Maximum Junction Temperature	T _{J(MAX)}	150	°C
Storage Temperature Range	T _{STG}	–55 to +150	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per EIA/JESD22-A114 ESD Machine Model tested per EIA/JESD22-A115

Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN6 1.2 x 1.2 mm, Thermal Resistance, Junction-to-Air Thermal Characterization Parameter, Junction-to-Lead (Pin 2)	θ_{JL}	170	°C/W

3. Single component mounted on 1 oz, FR4 PCB with 645mm2 Cu area.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Мах	Unit
Input Voltage	V _{IN}	1.9	5.25	V
Junction Temperature	TJ	-40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTIC

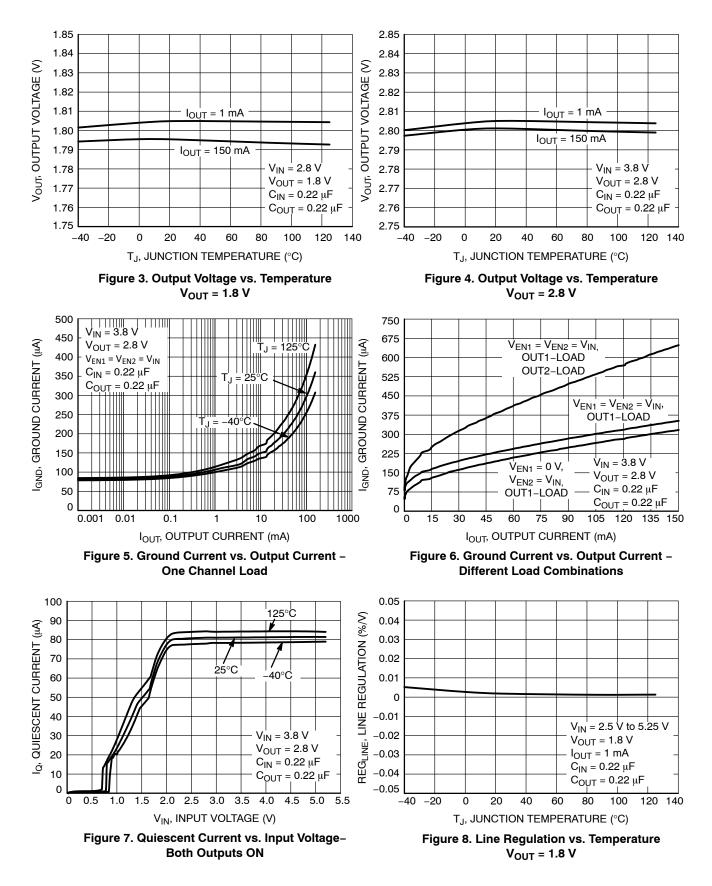
 $-40^{\circ}C \leq T_{J} \leq 125^{\circ}C; V_{IN} = V_{OUT(NOM)} + 1 \text{ V or } 2.5 \text{ V}, \text{ whichever is greater}; V_{EN} = 0.9 \text{ V}, I_{OUT} = 1 \text{ mA}, C_{IN} = C_{OUT} = 0.22 \text{ }\mu\text{F}. \text{ Typical values are at } T_{J} = +25^{\circ}C. \text{ Min/Max values are specified for } T_{J} = -40^{\circ}C \text{ and } T_{J} = 125^{\circ}C \text{ respectively}. \text{ (Note 4)}$

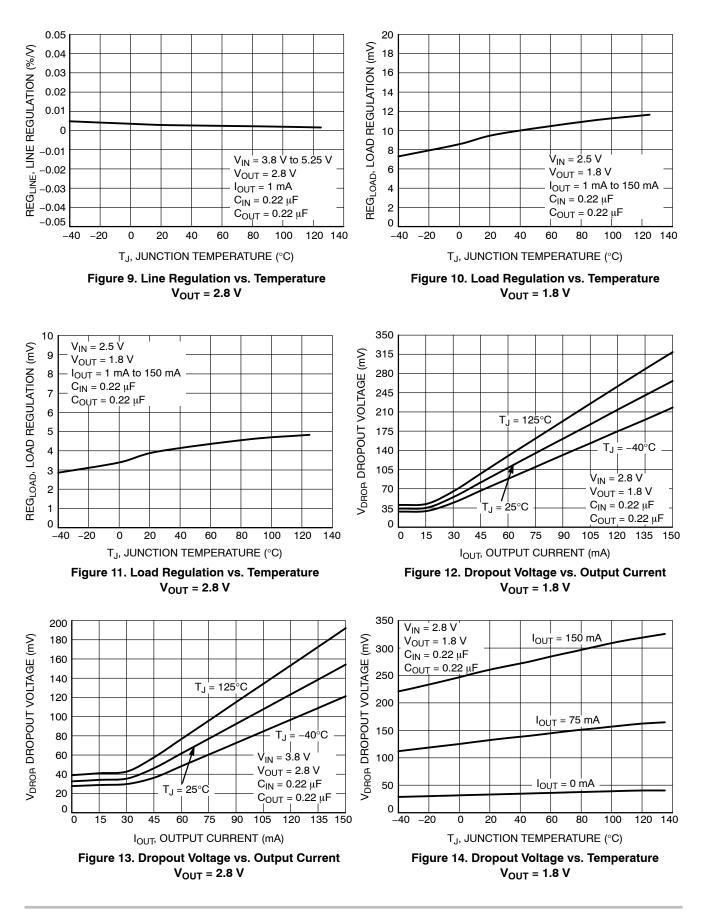
Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			Vin	1.9		5.25	V
Output Voltage Accuracy	1000 17 110500	V _{OUT} > 2 V	Vout	-2.8		+2.8	%
	$-40^{\circ}C \le T_J \le 125^{\circ}C$	$V_{OUT} \le 2 V$		-80		+80	mV
Line Regulation	Vout + 0.5 V or 2.5 V \leq Vin \leq	5 V	Reg _{LINE}		0.02	0.1	%/V
Load Regulation	IOUT = 1 mA to 150 mA		Reg _{LOAD}		15	50	mV
		V _{OUT(nom)} = 1.8 V			270	420	
Dropout Voltage (Note 5)	l _{out} = 150 mA	V _{OUT(nom)} = 3.0 V	V _{DO}		150	240	mV
		V _{OUT(nom)} = 3.3 V			140	240	
Output Current Limit	V _{OUT} = 90% V _{OUT(nom)}		ICL	150			mA
Quiescent Current	IOUT = 0 mA, EN1 = V_{IN} , EN2 = 0 V or EN2 = V_{IN} , EN1 = 0 V		lq		50	100	μΑ
	IOUT1 = IOUT2 = 0 mA, V _{EN1} =	lq		85	200	μA	
Shutdown current (Note 6)	$V_{EN} \leq 0.4$ V, V_{IN} = 5.25 V		Idis		0.1	1	μΑ
EN Pin Threshold Voltage High Threshold Low Threshold	VEN Voltage increasing VEN Voltage decreasing		Ven_hi Ven_lo	0.9		0.4	V
EN Pin Input Current	VEN = VIN = 5.25 V		IEN		0.3	1.0	μA
Power Supply Rejection Ratio	$\label{eq:VIN} \begin{array}{l} V_{IN} = V_{OUT+1} \; V \; \text{for} \; \; V_{OUT} > 2 \; V, \; V_{IN} = 2.5 \; V, \\ for \; V_{OUT} \leq 2 \; V, \; \text{lout} = 10 \; \text{mA} \end{array} \; f = 1 \; \text{kHz}$		PSRR		75		dB
Output Noise Voltage	f = 10 Hz to 100 kHz		VN		75		μV_{rms}
Active Discharge Resistance	$V_{IN} = 4 V, V_{EN} < 0.4 V$		R _{DIS}		50		Ω
Thermal Shutdown Temperature	ermal Shutdown Temperature Temperature increasing from T _J = +25°C		Tsd		160		°C
Thermal Shutdown Hysteresis	Temperature falling from Tsp)	TSDH	_	20	-	°C

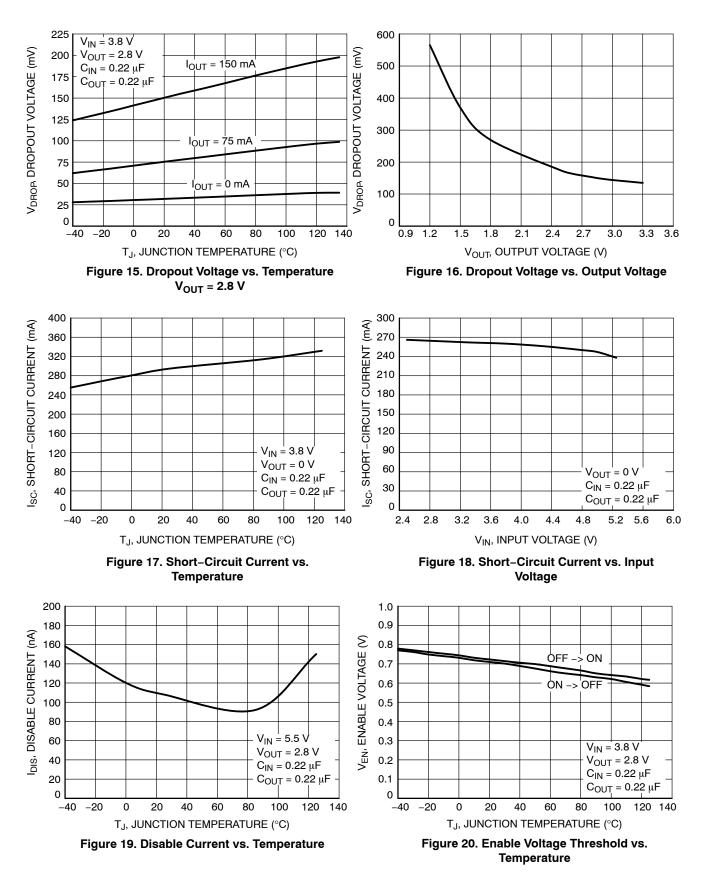
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

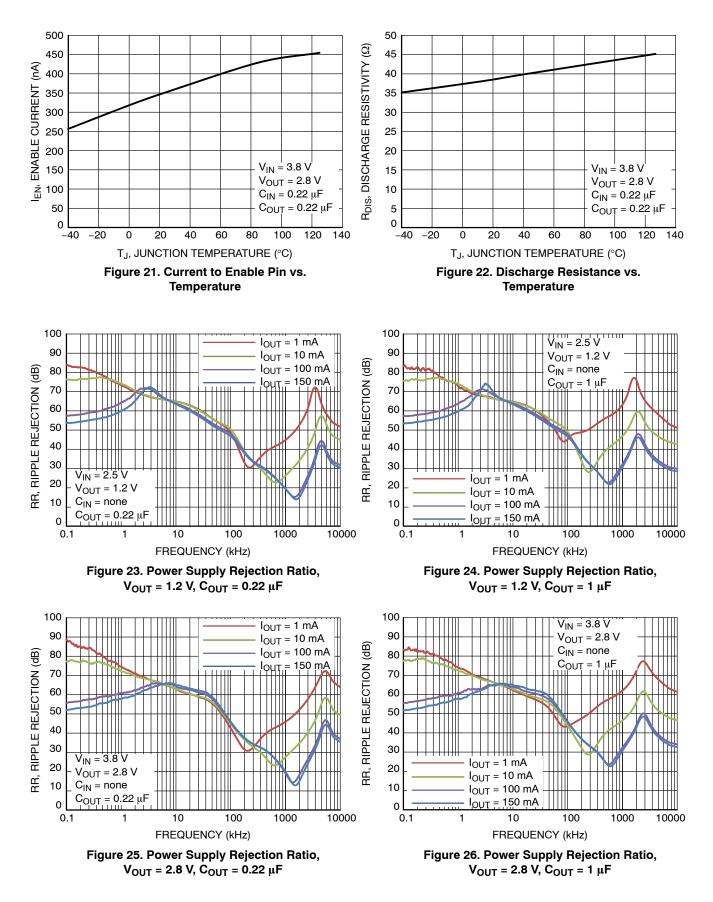
Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

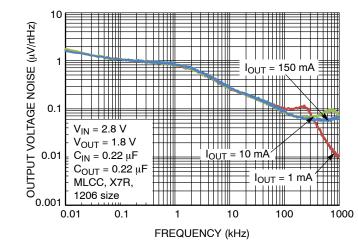
5. Characterized when V_{OUT} falls 100 mV below the regulated voltage at $V_{IN} = V_{OUT(NOM)} + 1 V$. 6. Shutdown Current is the current flowing into the IN pin when the device is in the disable state.





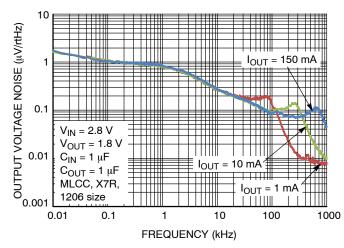






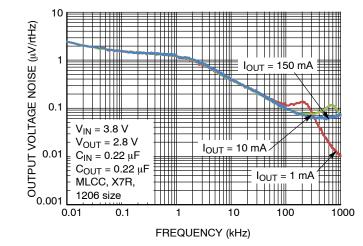
	RMS Output Noise (μV)		
lout	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	68.07	67.07	
10 mA	67.30	66.31	
150 mA	69.74	68.80	

Figure 27. Output Voltage Noise Spectral Density for V_{OUT} = 1.8 V, C_{OUT} = 220 nF



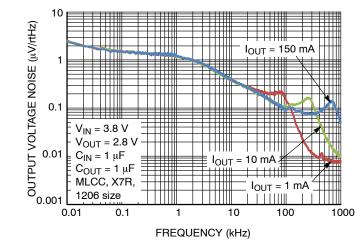
	RMS Output Noise (μV)		
IOUT	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	76.23	75.33	
10 mA	67.12	66.12	
150 mA	69.06	68.12	

Figure 28. Output Voltage Noise Spectral Density for V_{OUT} = 1.8 V, C_{OUT} = 1 μ F



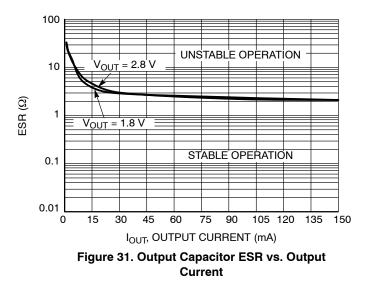
	RMS Output Noise (µV)		
IOUT	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	93.42	91.99	
10 mA	92.88	91.45	
150 mA	94.67	93.26	

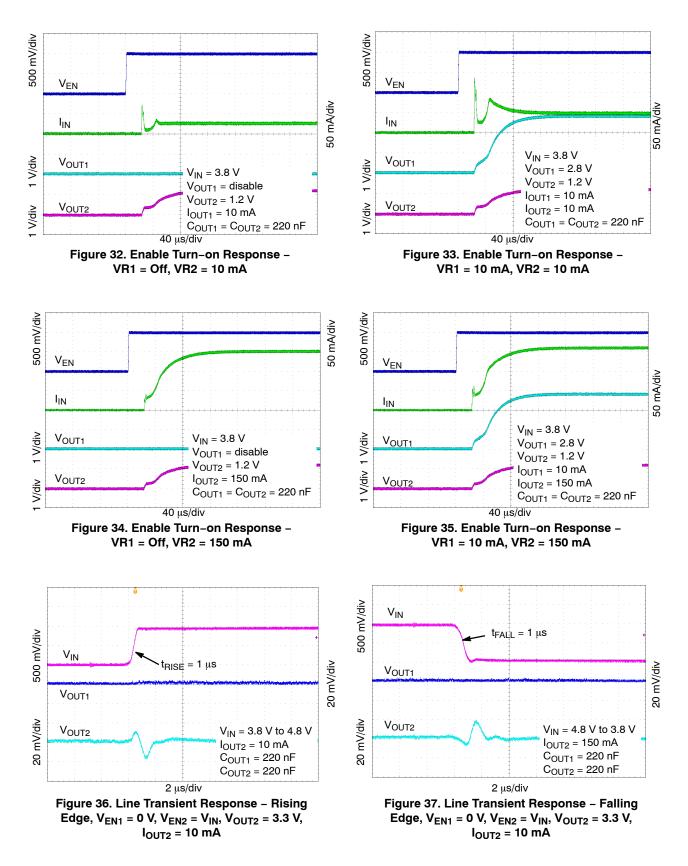


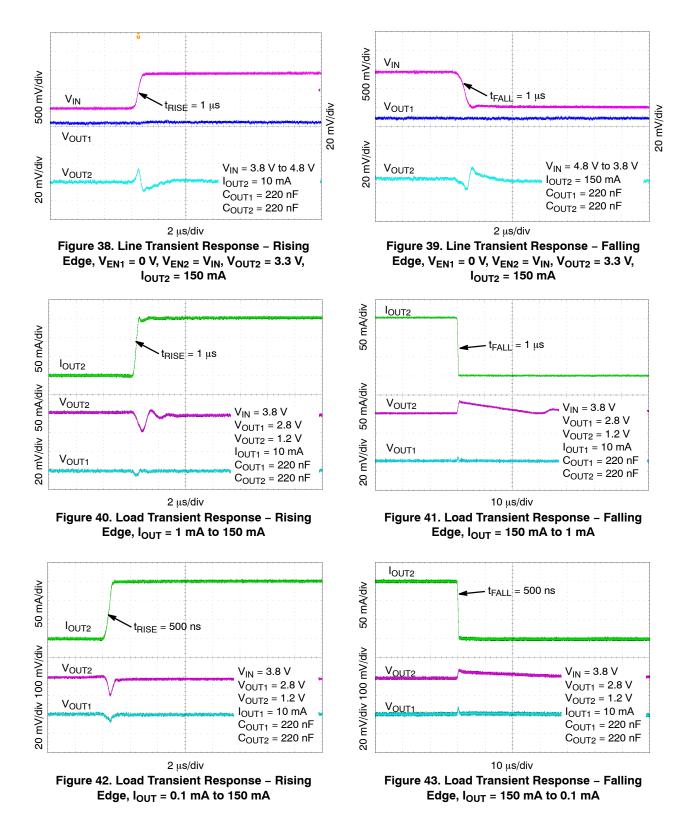


	RMS Output Noise (μV)		
lout	10 Hz – 100 kHz	100 Hz – 100 kHz	
1 mA	102.14	100.86	
10 mA	93.03	91.59	
150 mA	94.74	93.12	

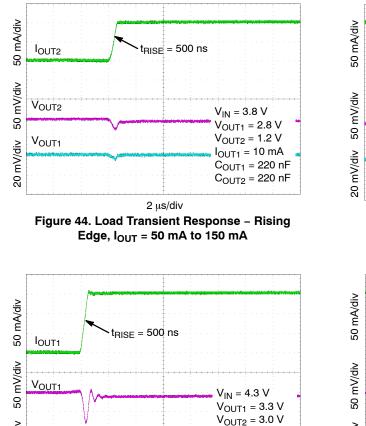








TYPICAL CHARACTERISTICS



 $I_{OUT1} = 10 \text{ mA}$

C_{OUT1} = 220 nF

C_{OUT2} = 220 nF

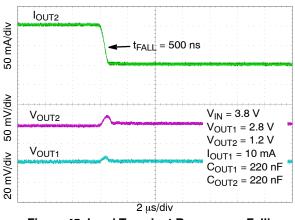


Figure 45. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 50 mA

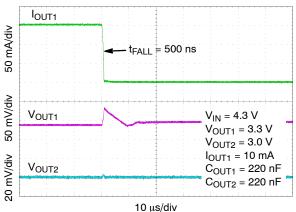
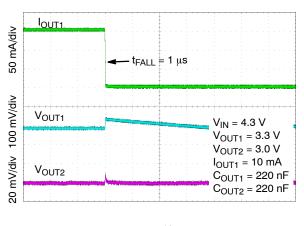
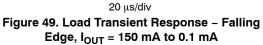
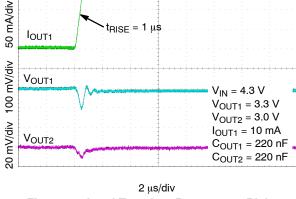


Figure 48. Load Transient Response – Falling Edge, I_{OUT} = 150 mA to 1 mA







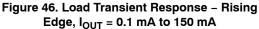
2 μs/div

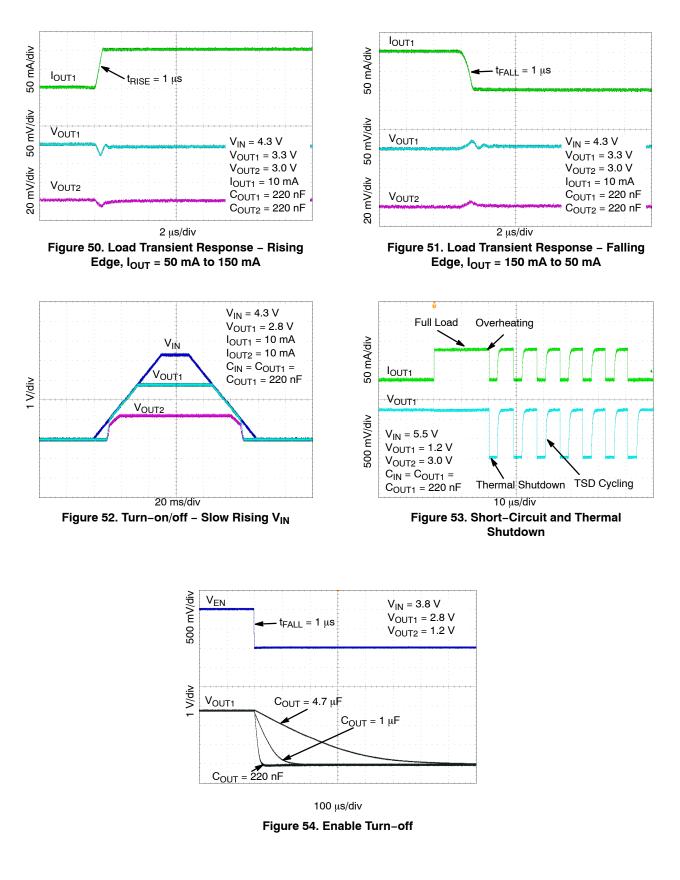
Figure 47. Load Transient Response - Rising

Edge, I_{OUT} = 1 mA to 150 mA

20 mV/div

V_{OUT2}





APPLICATIONS INFORMATION

General

The NCV8152 is a dual output high performance 150 mA Low Dropout Linear Regulator. This device delivers very high PSRR (75 dB at 1 kHz) and excellent dynamic performance as load/line transients. In connection with low quiescent current this device is very suitable for various battery powered applications such as tablets, cellular phones, wireless and many others. Each output is fully protected in case of output overload, output short circuit condition and overheating, assuring a very robust design. The NCV8152 device is housed in XDFN–6 1.2 mm x 1.2 mm package which is useful for space constrains application.

Input Capacitor Selection (CIN)

It is recommended to connect at least a 0.22 μ F Ceramic X5R or X7R capacitor as close as possible to the IN pin of the device. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the min. or max. ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes. Larger input capacitor may be necessary if fast and large load transients are encountered in the application.

Output Decoupling (COUT)

The NCV8152 requires an output capacitor for each output connected as close as possible to the output pin of the regulator. The recommended capacitor value is $0.22 \ \mu$ F and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The NCV8152 is designed to remain stable with minimum effective capacitance of 0.15 μ F to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0201 the effective capacitance drops rapidly with the applied DC bias.

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the C_{OUT} but the maximum value of ESR should be less than 2 Ω . Larger output capacitors and lower ESR could improve the load transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

Enable Operation

The NCV8152 uses the dedicated EN pin for each output channel. This feature allows driving outputs separately.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned–off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage V_{OUT} is pulled to GND through a 50 Ω resistor. In the disable state the device consumes as low as typ. 10 nA from the $\ensuremath{V_{\text{IN}}}$.

If the EN pin voltage >0.9 V the device is guaranteed to be enabled. The NCV8152 regulates the output voltage and the active discharge transistor is turned-off.

The both EN pin has internal pull-down current source with typ. value of 300 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

Output Current Limit

Output Current is internally limited within the IC to a typical 280 mA. The NCV8152 will source this amount of current measured with a voltage drops on the 90% of the nominal V_{OUT} . If the Output Voltage is directly shorted to ground ($V_{OUT} = 0$ V), the short circuit protection will limit the output current to 300 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration. This protection works separately for each channel. Short circuit on the one channel do not influence second channel which will work according to specification.

Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ($T_{SD} - 160^{\circ}$ C typical), Thermal Shutdown event is detected and the affected channel is turn-off. Second channel still working. The channel which is overheated will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ($T_{SDU} - 140^{\circ}$ C typical). Once the device temperature falls below the 140°C the appropriate channel is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking. The long duration of the short circuit condition to some output channel could cause turn-off other output when heat sinking is not enough and temperature of the other output reach T_{SD} temperature.

Power Dissipation

As power dissipated in the NCV8152 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part. For reliable operation, junction temperature should be limited to $+125^{\circ}$ C.

The maximum power dissipation the NCV8152 can handle is given by:

$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = \frac{\left[125^{\circ}\mathsf{C} - \mathsf{T}_{\mathsf{A}}\right]}{\theta_{\mathsf{J}\mathsf{A}}} \tag{eq. 1}$$

The power dissipated by the NCV8152 for given application conditions can be calculated from the following equations:

$$\begin{split} \mathsf{P}_{\mathsf{D}} &\approx \mathsf{V}_{\mathsf{IN}} \times \mathsf{I}_{\mathsf{GND}} + \mathsf{I}_{\mathsf{OUT1}} \big(\mathsf{V}_{\mathsf{IN}} - \mathsf{V}_{\mathsf{OUT1}} \big) \\ &+ \mathsf{I}_{\mathsf{OUT2}} \big(\mathsf{V}_{\mathsf{IN}} - \mathsf{V}_{\mathsf{OUT2}} \big) \end{split} \tag{eq. 2}$$

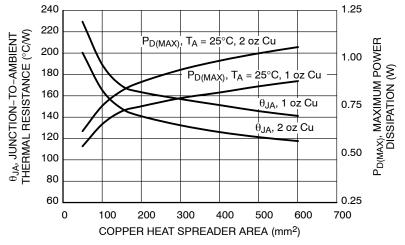


Figure 55. θ_{JA} vs. Copper Area (XDFN-6)

Reverse Current

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that $V_{OUT} > V_{IN}$. Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

Power Supply Rejection Ratio

The NCV8152 features very good Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range 100 kHz – 10 MHz can be tuned by the selection of C_{OUT} capacitor and proper PCB layout.

Turn-On Time

The turn-on time is defined as the time period from EN assertion to the point in which V_{OUT} will reach 98% of its

nominal value. This time is dependent on various application conditions such as $V_{OUT(NOM)}$, C_{OUT} , T_A .

PCB Layout Recommendations

To obtain good transient performance and good regulation characteristics place input and output capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 capacitors. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad should be tied the shortest path to the GND pin.

Device	Voltage Option (OUT1/OUT2)	Marking	Marking Rotation	Package	Shipping [†]
NCV8152MX180150TCG	1.8 V/1.5 V	AN	0°		
NCV8152MX180180TCG	1.8 V/1.8 V	AJ	0°	XDFN-6	
NCV8152MX180280TCG	1.8 V/2.8 V	5	180°		XDFN-6
NCV8152MX280180TCG	2.8 V/1.8 V	6	270°	(Pb-Free)	3000 / Tape & Reel
NCV8152MX300180TCG	3.0 V/1.8 V	L	90°		
NCV8152MX330180TCG	3.3 V/1.8 V	R	90°		

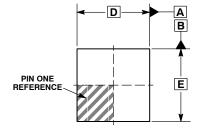
ORDERING INFORMATION

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

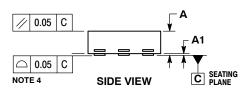


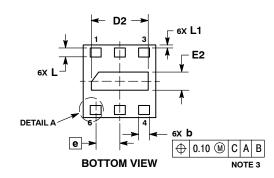


SCALE 4:1



TOP VIEW





ISSUE C

DETAIL A OPTIONAL CONSTRUCTION

XDFN6 1.20x1.20, 0.40P CASE 711AT

DATE 04 DEC 2015

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 5. DIMENSION: ADDRESSION: MILLIMETERS.

3. DIMENSION b APPLIES TO THE PLATED TERMINALS.

COPLANARITY APPLIES TO THE PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	TYP	MAX	
Α	0.30	0.37	0.45	
A1	0.00	0.03	0.05	
b	0.13	0.18	0.23	
D	1.15	1.20	1.25	
D2	0.84	0.94	1.04	
E	1.15	1.20	1.25	
E2	0.20	0.30	0.40	
е	0.40 BSC			
L	0.15	0.20	0.25	
L1	0.00	0.05	0.10	

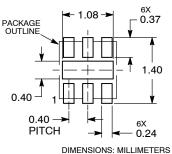
GENERIC **MARKING DIAGRAM***

хх м
0

XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

RECOMMENDED **MOUNTING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON76141F	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	XDFN6, 1.20 X 1.20, 0.40P		PAGE 1 OF 1
ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.			

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative